



Description

The AONR21321-HXY uses advanced trench technology excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

$V_{DS} = -30V, I_D = -50A$

$R_{DS(ON)} < 15m\Omega @ V_{GS} = -10V$

$R_{DS(ON)} < 25m\Omega @ V_{GS} = -4.5V$

High Power and current handling capability

Lead free product is acquired

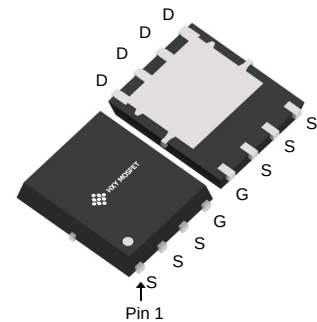
Surface mount package

Application

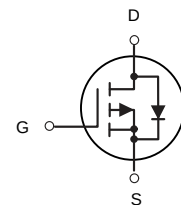
PWM applications

Load switch

Power management



DFN5X6-8L



P-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AONR21321-HXY	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ($T_C = 25^\circ C$)	-50	A
	Drain Current-Continuous ($T_C = 100^\circ C$)	-24	
IDM	Drain Current-Pulsed (Note 1)	-80	A
P _D	Maximum Power Dissipation ($T_C = 25^\circ C$)	3	W
	Maximum Power Dissipation ($T_C = 100^\circ C$)	1.3	
EAS	Single pulse avalanche energy (Note 5)	231	mJ
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 2)	41.67	°C/W



Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-33	-	V
Zero Gate Voltage Drain Current	$IDSS$	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	$IGSS$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-10A$	-	9	15	m Ω
		$V_{GS}=-4.5V, I_D=-7A$	-	18	25	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-10A$	-	20	-	S
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$	-	1750	-	PF
Output Capacitance	C_{oss}		-	215	-	PF
Reverse Transfer Capacitance	C_{rss}		-	180	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-10A,$ $V_{GS}=-10V, R_{GEN}=1\Omega$	-	9	-	nS
Turn-on Rise Time	t_r		-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	28	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-10A, V_{GS}=-10V$	-	24	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	nC
Gate-Drain Charge	Q_{gd}		-	6	-	nC
Diode Forward Current ^(Note 2)	I_S		-	-	-12	A
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=-12A$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_j=25^{\circ}\text{C}, V_{DD}=-15V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=-34A$



Typical Electrical and Thermal Characteristics

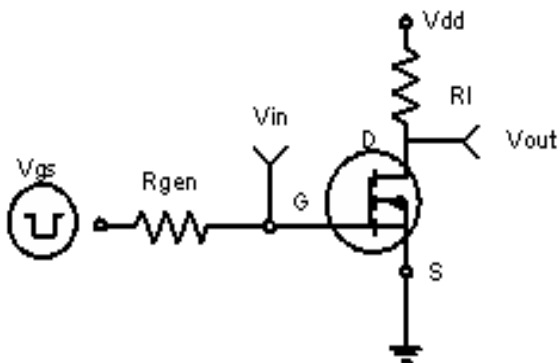


Figure 1: Switching Test Circuit

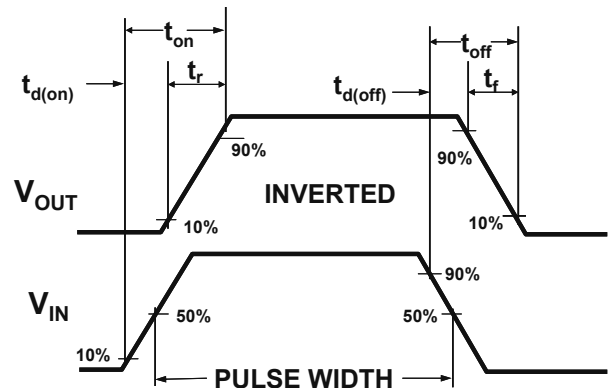


Figure 2: Switching Waveforms

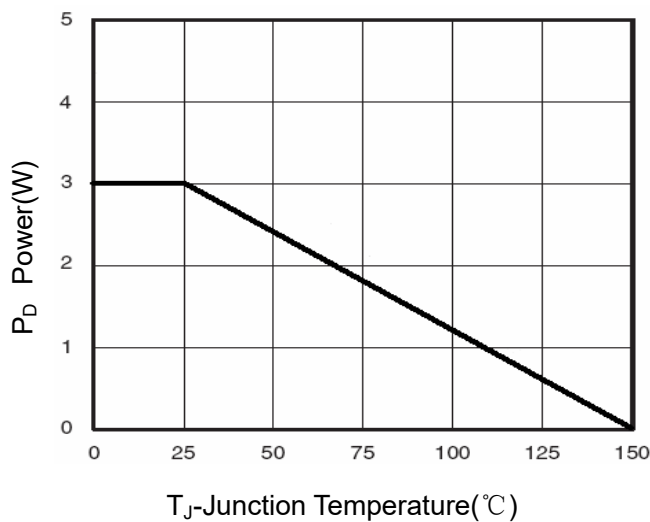


Figure 3 Power Dissipation

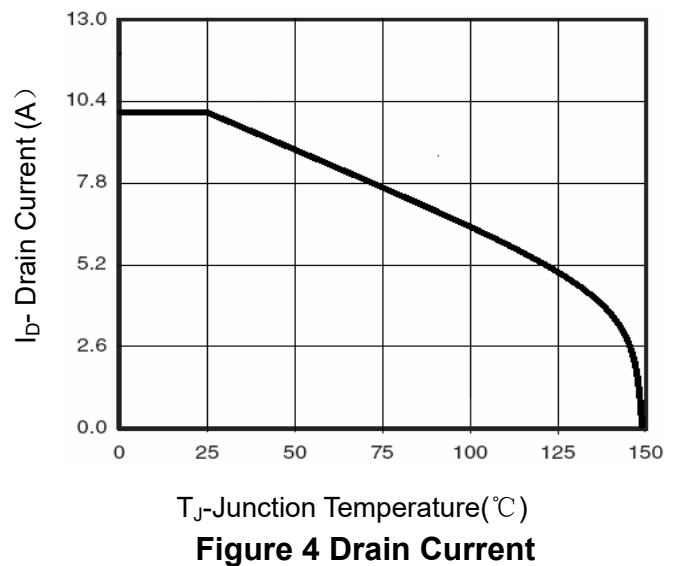


Figure 4 Drain Current

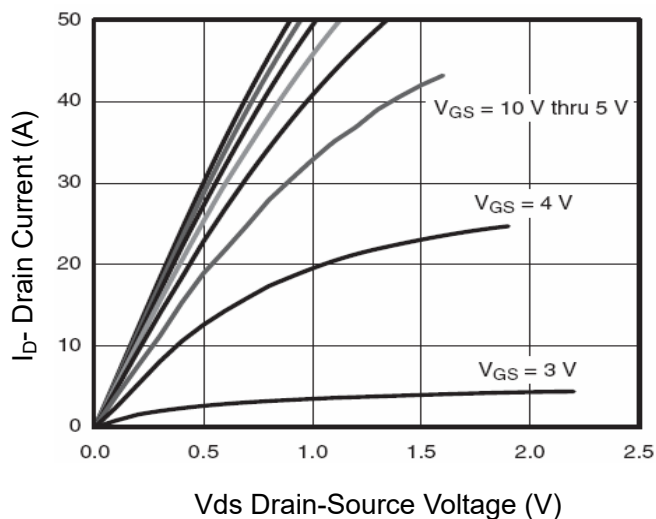


Figure 5 Output Characteristics

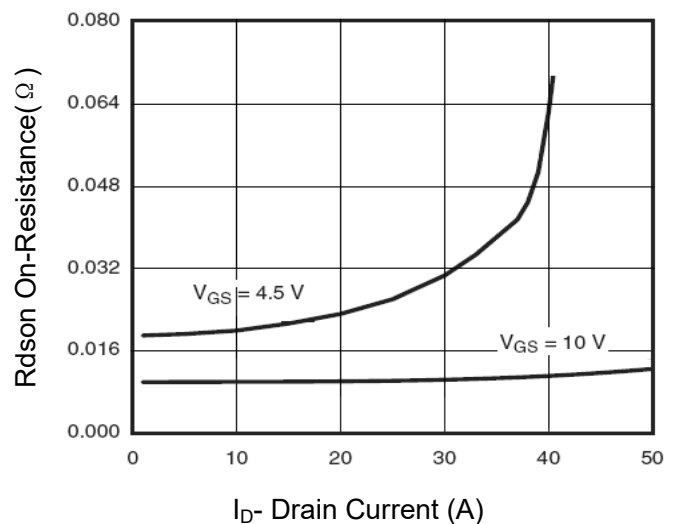


Figure 6 Drain-Source On-Resistance



Figure 5 Output Characteristics

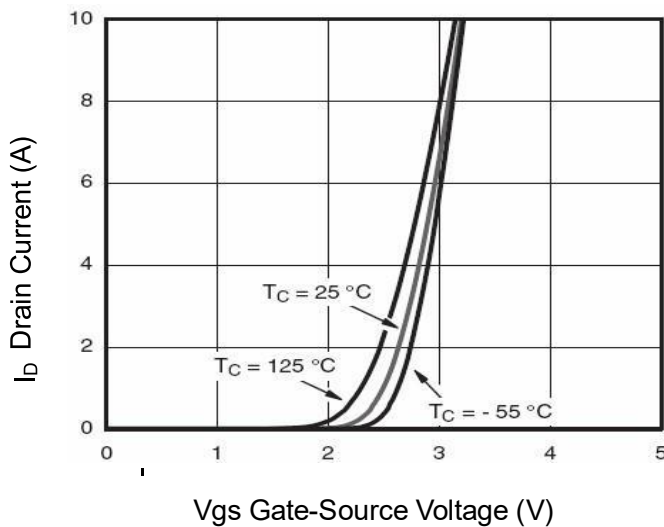


Figure 7 Transfer Characteristics

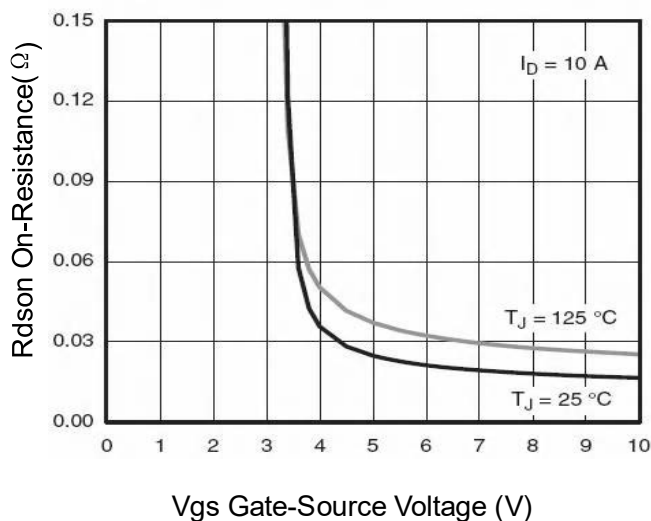


Figure 9 Rdson vs Vgs

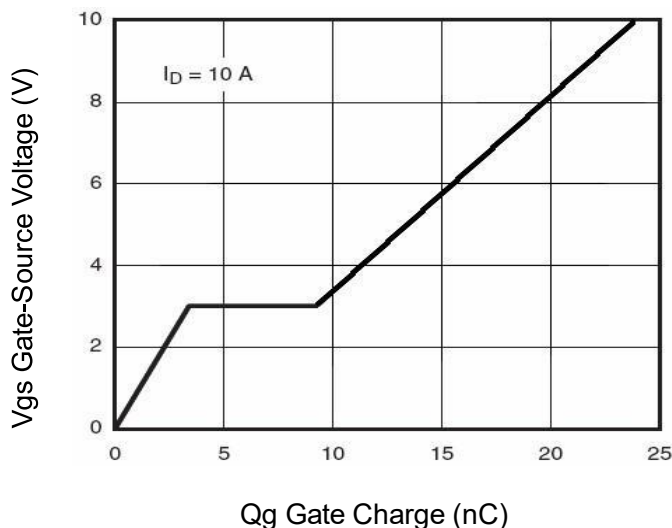


Figure 11 Gate Charge

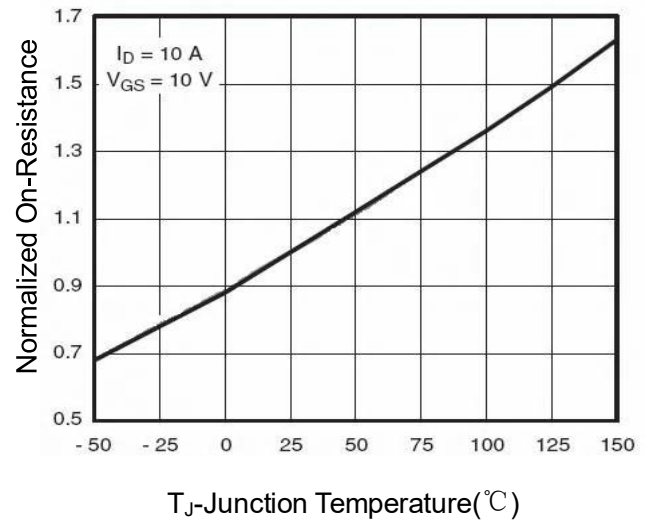


Figure 8 Drain-Source On-Resistance

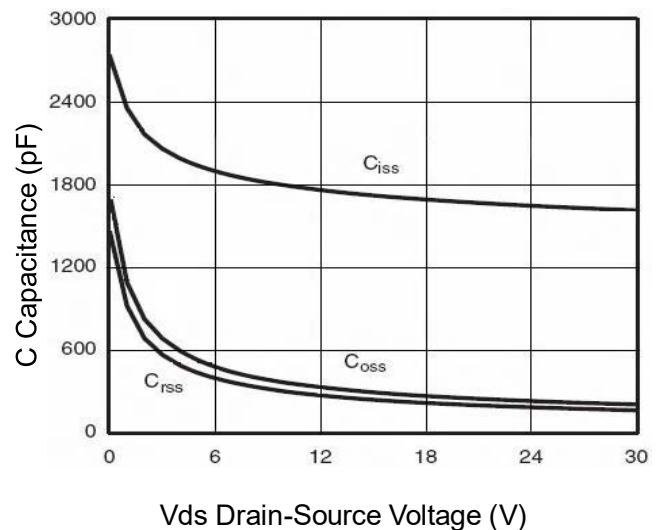


Figure 10 Capacitance vs Vds

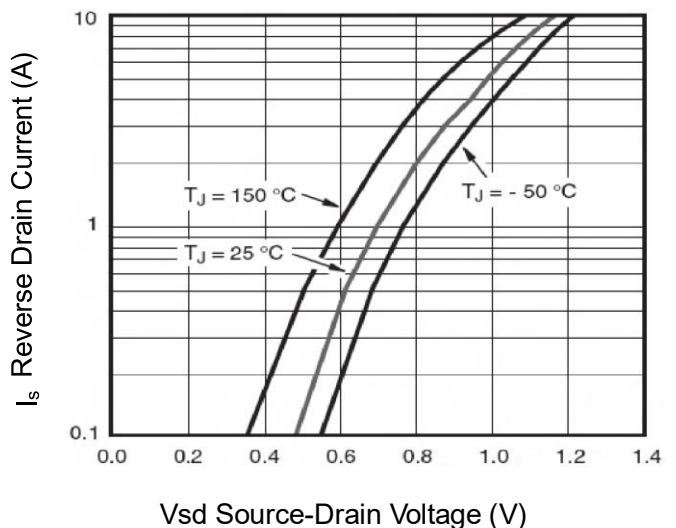


Figure 12 Source- Drain Diode Forward

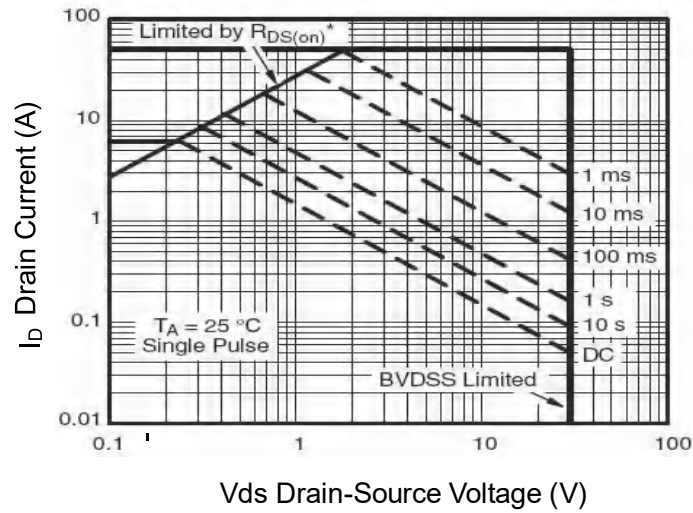


Figure 13 Safe Operation Area

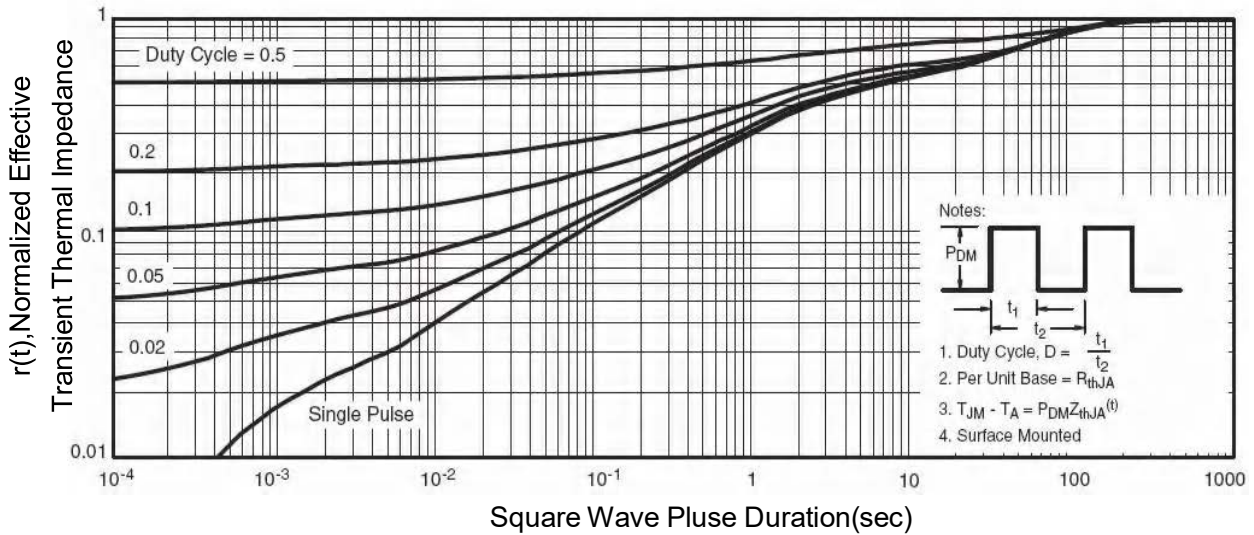
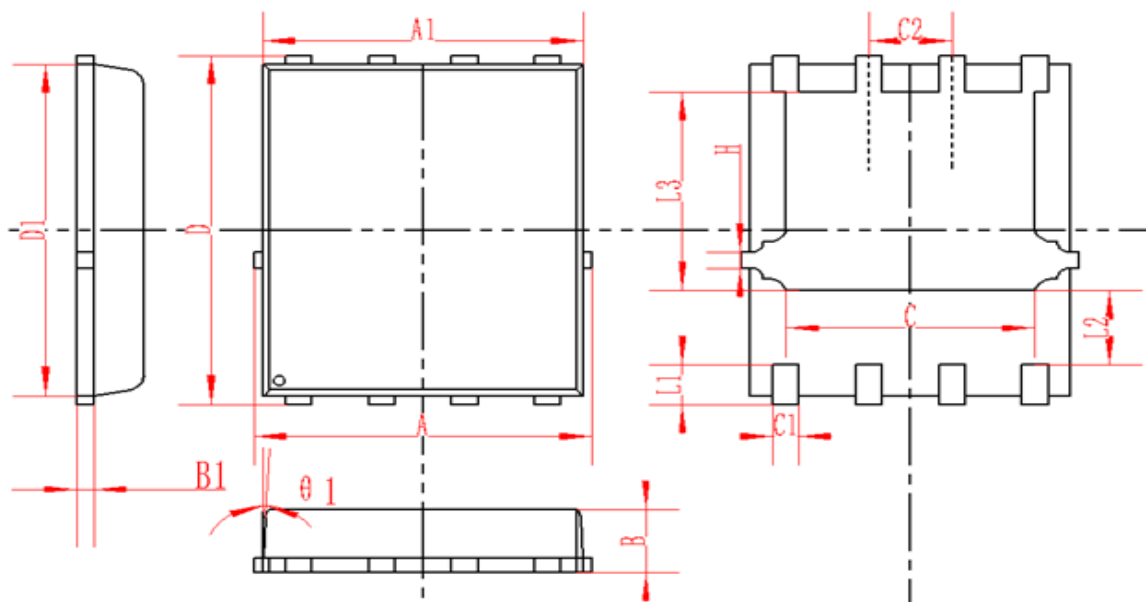


Figure 14 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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